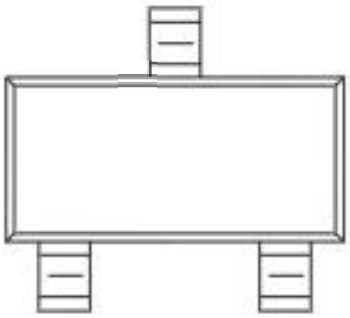
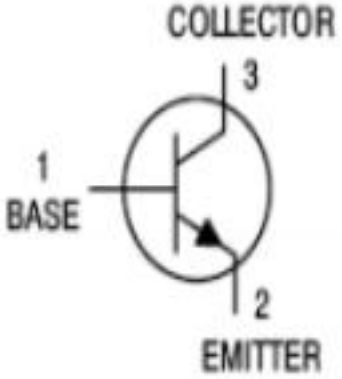
2SC2712 TRANSI STOR (NPN)

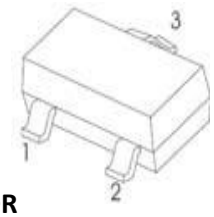
MARKING:



Equivalent Circuit:



SOT-23



1.BASE
2.EMITTER
3.COLLECTOR

FEATURES:
※ Complimentary to 2SA1162
※ LOW noise NF= 1DB(Typ) 10dB (MAX)

MAXIMUM RATINGS (Ta=25℃ unless otherwise noted)

Parameter	Symbol	Value	Unit
Collector-Base Voltage	VCBO	60	V
Collector-Emitter Voltage	VCEO	50	V
Emitter-Base Voltage	VEBO	5	V
Collector Current	IC	150	mA
Collector Power Dissipation	PC	150	mW
Thermal Resistance From Junction To Ambient	RΘJA	833	℃/W
Junction Temperature	Tj	150	℃
Storage Temperature	Tstg	-55～+150	℃

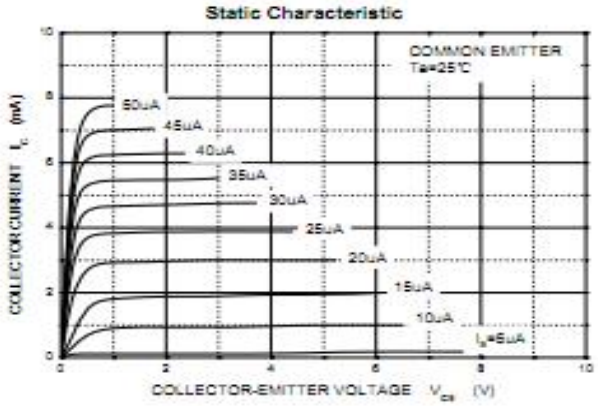
ELECTRICAL CHARACTERISTICS (Ta=25℃ unless otherwise specified)

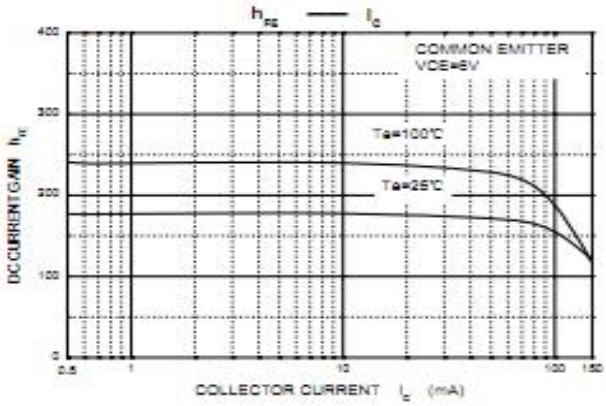
Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Collector-base breakdown voltage	V(BR)CBO	IC= 100μA, IE=0	60			V
Collector-emitter breakdown voltage	V(BR)CEO	IC= 1mA, IB=0	50			V
Emitter-base breakdown voltage	V(BR)EBO	IE=100μA, IC=0	5			V
Collector cut-off current	ICBO	VCB=60 V , IE=0			0.1	μA
Emitter cut-off current	IEBO	VEB= 5V , IC=0			0.1	μA
DC current gain	hFE	VCE=6V, IC= 2mA	70		700	
Collector-emitter saturation voltage	VCE(sat)	IC=100 mA, IB= 10mA		0.1	0.25	V
Base-emitter saturation voltage	VBE(sat)	IC=100 mA, IB= 10mA			1	V
Transition frequency	fT	VCE=10V, IC= 1mA f=1MHz	80			MHz
Collector Output Capacitance	Cob	VCE=10V, IE= 0 f=1MHz		2.0	3.5	pf
Noise Figure	NF	VCE=6V, IC= 0.1mA Rg=10kΩ; f=1KHz		1.0	10	dB

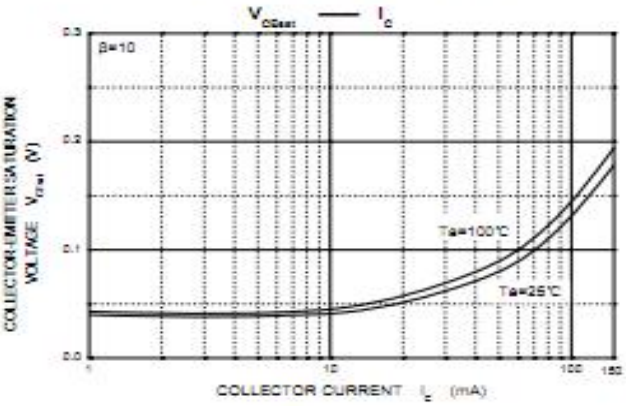
CLASSIFICATION OF hFE

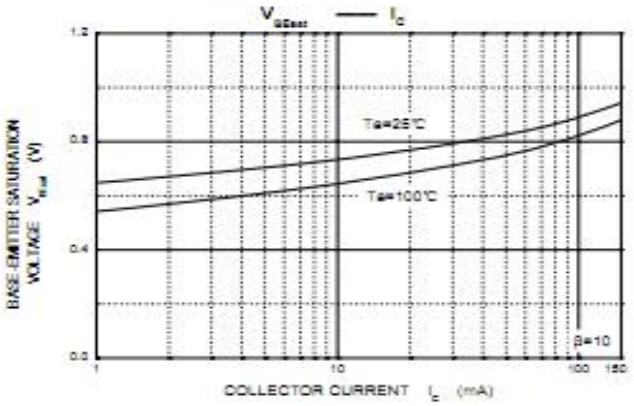
Rank	O	Y	GR	BL
Range	70-140	120-240	200-400	350-700
Marking	LO	LY	LG	LL

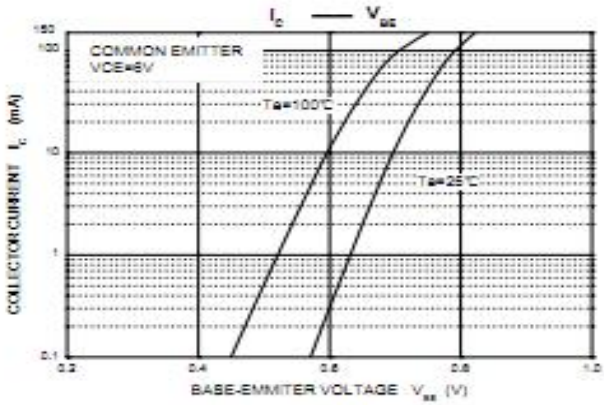
TYPICAL ELEC TRICAL AND THERMAL CHARACTERISTICS

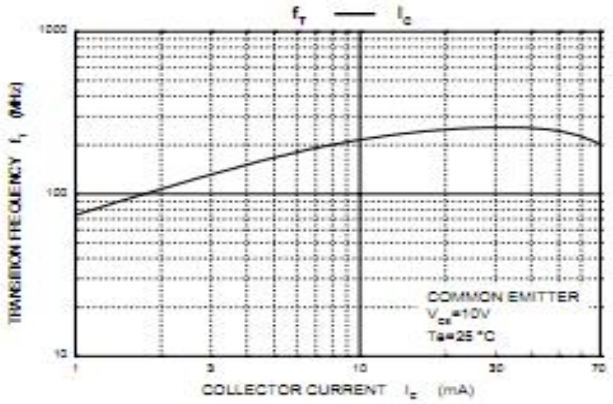


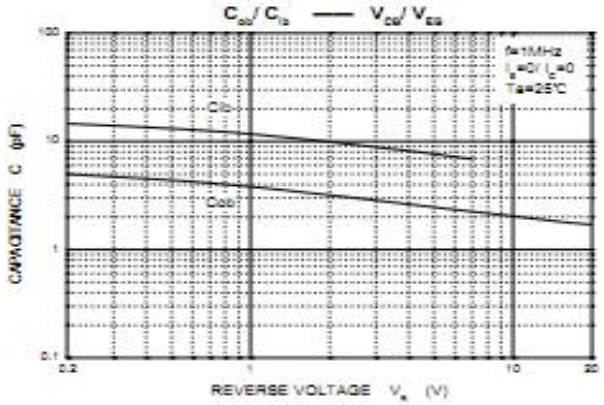


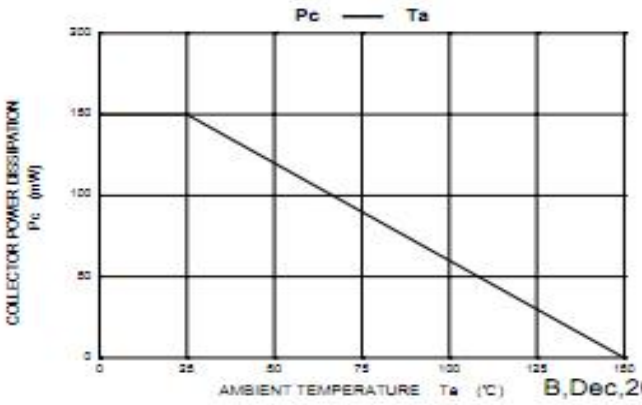












B,Dec,201